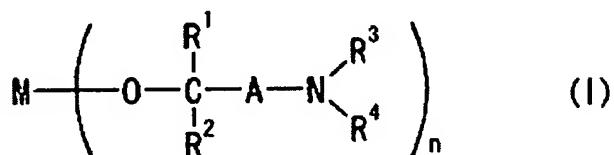


AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): An alkoxide compound represented by general formula (I):



wherein one of R^1 and R^2 represents an alkyl group having 1 to 4 carbon atoms, and the other represents a hydrogen atom or an alkyl group having 1 to 4 carbon atoms; R^3 and R^4 each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a silicon atom or a hafnium atom; and n represents 4.

2. (original): The alkoxide compound according to claim 1, wherein A in general formula (I) is a methylene group.

3. (currently amended): The alkoxide compound according to claim 1 ~~or 2~~, wherein M in general formula (I) is a silicon atom.

4. (currently amended): The alkoxide metal compound according to claim 1 ~~or 2~~, wherein M in general formula (I) is a hafnium atom.

5. (currently amended): A material for thin film formation comprising the alkoxide compound according to ~~any one of~~ ~~claims 1 to 4~~ claim 1.

6. (original): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 5, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.

7. (new): The alkoxide compound according to claim 2, wherein M in general formula (I) is a silicon atom.

8. (new): The alkoxide metal compound according to claim 4, wherein M in general formula (I) is a hafnium atom.

9. (new): A material for thin film formation comprising the alkoxide compound according to claim 2.

10. (new): A material for thin film formation comprising the alkoxide compound according to claim 3.

11. (new): A material for thin film formation comprising the alkoxide compound according to claim 4.

12. (new): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 9, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.

13. (new): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 10, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.

14. (new): A process for thin film formation comprising vaporizing the material for thin film formation according to claim 11, introducing the resulting vapor containing the

alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.